



9NM50-S

Power MOSFET

9.0A, 500V N-CHANNEL SUPER-JUNCTION MOSFET

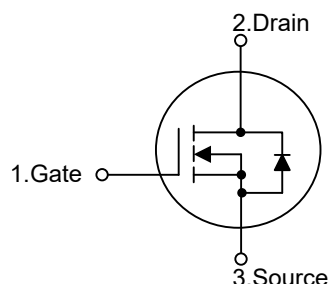
DESCRIPTION

The **UTC 9NM50-S** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)} \leq 0.43 \Omega @ V_{GS}=10V, I_D=4.5A$
- * High switching Speed
- * 100% avalanche tested
- * Improved dv/dt capability

SYMBOL

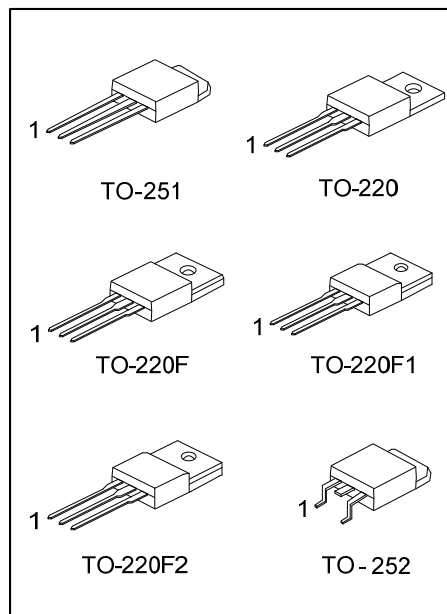


ORDERING INFORMATION

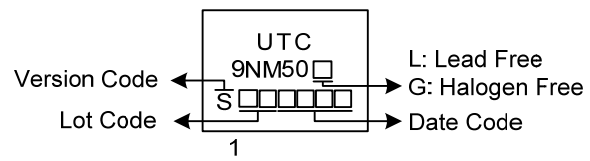
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
9NM50L-S-TA3-T	9NM50G-S-TA3-T	TO-220	G	D	S	Tube
9NM50L-S-TF1-T	9NM50G-S-TF1-T	TO-220F1	G	D	S	Tube
9NM50L-S-TF2-T	9NM50G-S-TF2-T	TO-220F2	G	D	S	Tube
9NM50L-S-TF3-T	9NM50G-S-TF3-T	TO-220F	G	D	S	Tube
9NM50L-S-TM3-T	9NM50G-S-TM3-T	TO-251	G	D	S	Tube
9NM50L-S-TN3-R	9NM50G-S-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

9NM50G-S-TA3-T	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2, TM3: TO-251, TN3: TO-252 (3) Version S (4) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DS}	500	V
Gate-Source Voltage		V_{GS}	± 30	V
Drain Current	Continuous	I_D	9	A
	Pulsed (Note 2)	I_{DM}	36	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	112	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	8.5	V/ns
Power Dissipation	TO-220	P_D	140	W
	TO-220F/TO-220F1		47	W
	TO-251/TO-252		56	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 100\text{mH}$, $I_{AS} = 1.5\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 9.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL CHARACTERISTICS

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2			
	TO-251/TO-252		110	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	θ_{JC}	0.89	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.66	$^\circ\text{C}/\text{W}$
	TO-251/TO-252		2.23 (Note)	$^\circ\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate P_c board, 2oz copper, with 1inch square copper plate.

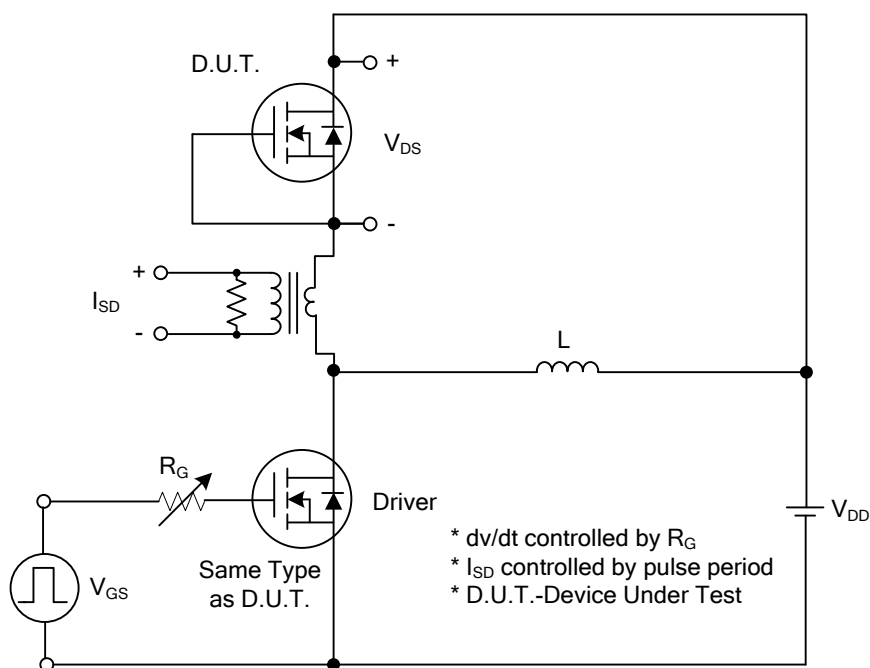
■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250μA, V _{GS} =0V	500			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =500V, V _{GS} =0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}	V _{GS} =+30V			+100	nA
	Reverse		V _{GS} =-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =4.5A			0.43	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =50V, f=1.0MHz		506		pF
Output Capacitance		C _{OSS}			172		pF
Reverse Transfer Capacitance		C _{RSS}			14		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =400V, V _{GS} =10V, I _D =9.0A (Note 1, 2)		38		nC
Gate to Source Charge		Q _{GS}			16		nC
Gate to Drain Charge		Q _{GD}			12		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =9.0A, R _G =25Ω (Note 1, 2)		9		ns
Rise Time		t _R			30		ns
Turn-OFF Delay Time		t _{D(OFF)}			68		ns
Fall-Time		t _F			30		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				9	A
Maximum Body-Diode Pulsed Current		I _{SM}				36	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =9.0A, V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)		t _{rr}	I _S =9.0A, V _{GS} =0V,		277		ns
Reverse Recovery Charge		Q _{rr}	dl _F /dt = 100 A/μs		3.09		μC

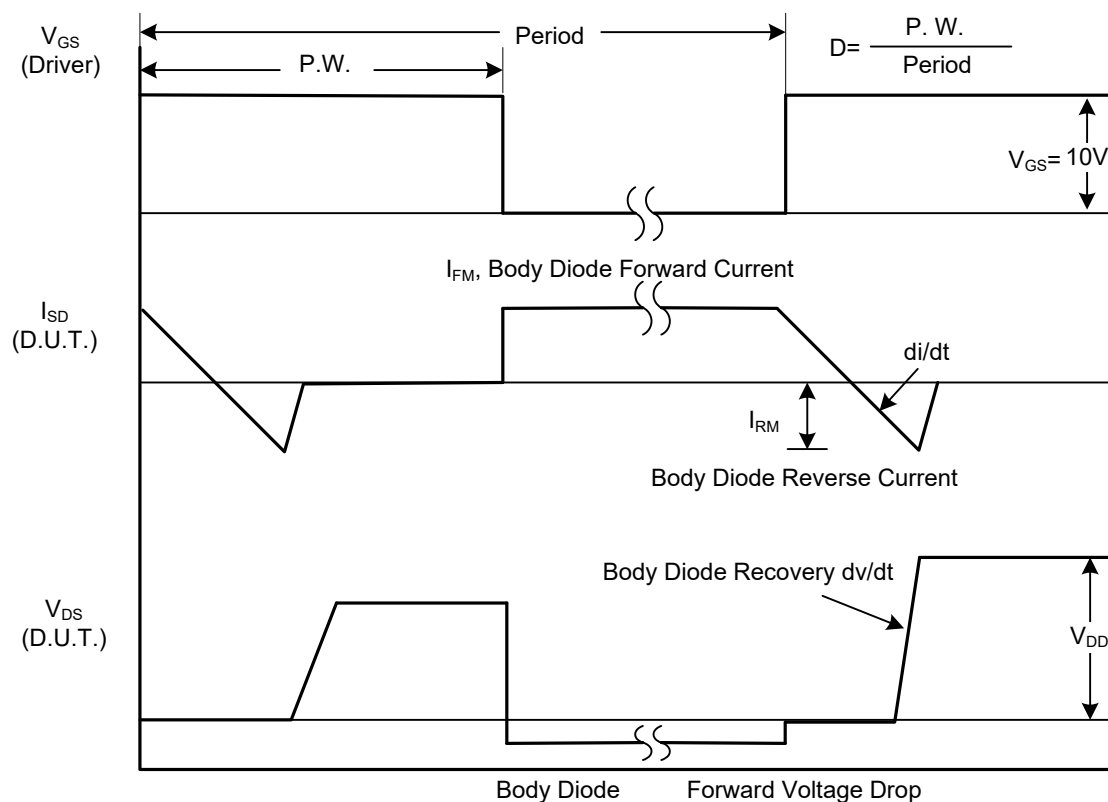
Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

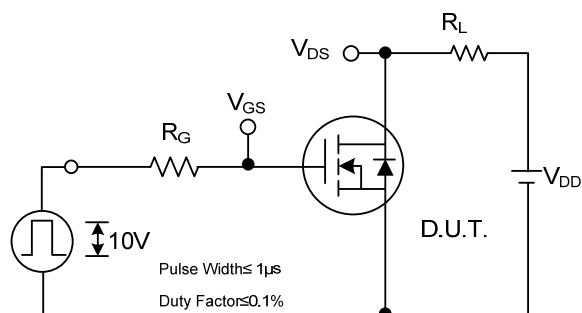


Peak Diode Recovery dv/dt Test Circuit

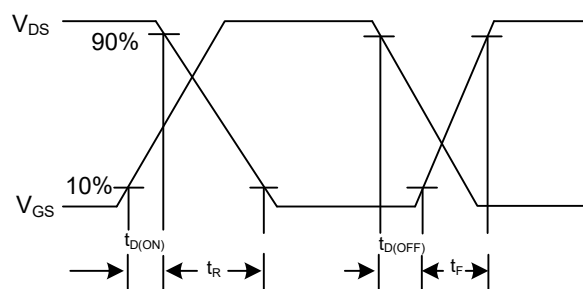


Peak Diode Recovery dv/dt Waveforms

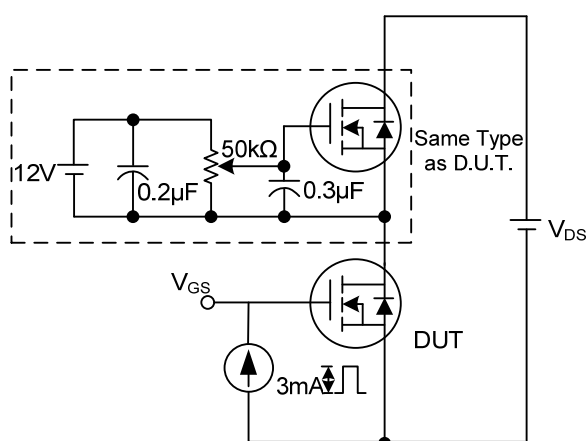
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



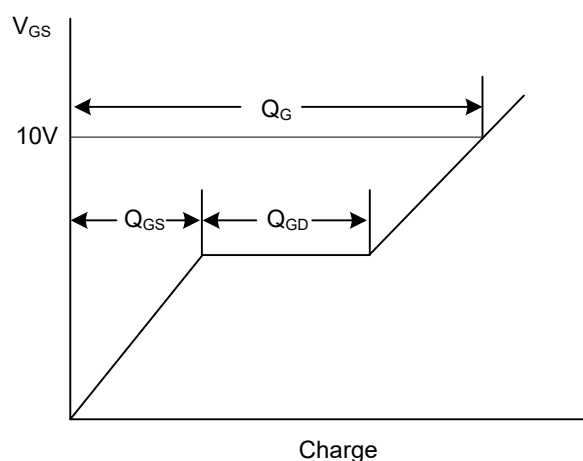
Switching Test Circuit



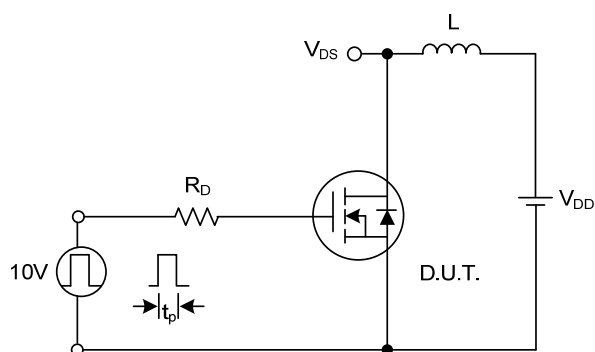
Switching Waveforms



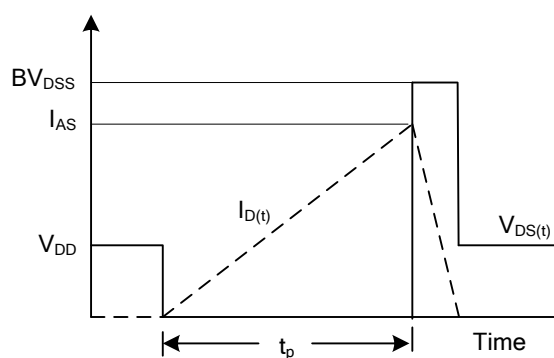
Gate Charge Test Circuit



Gate Charge Waveform

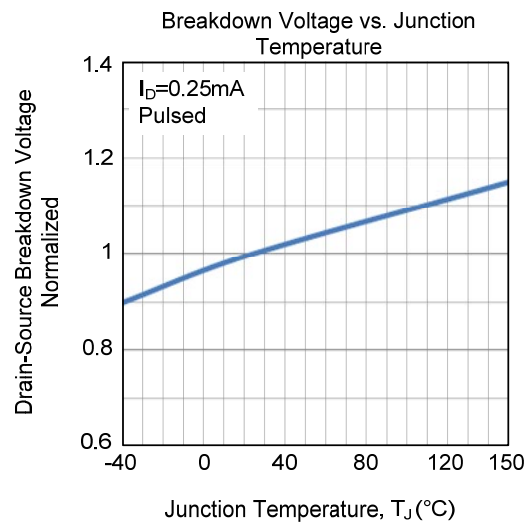
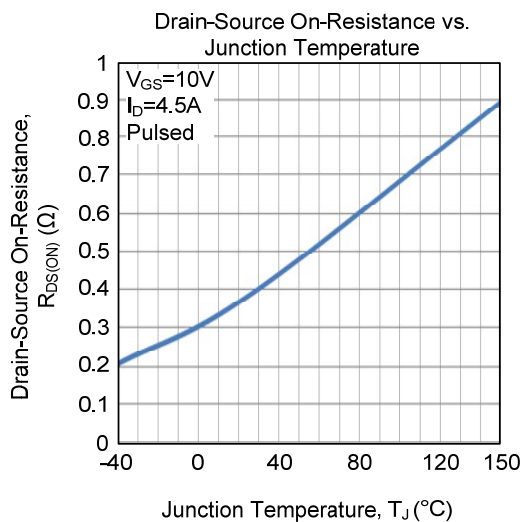
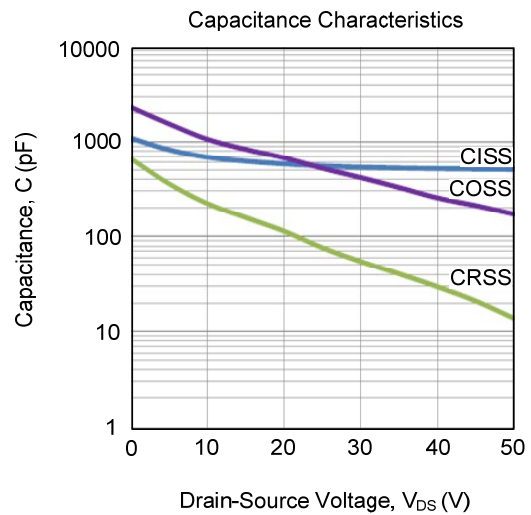
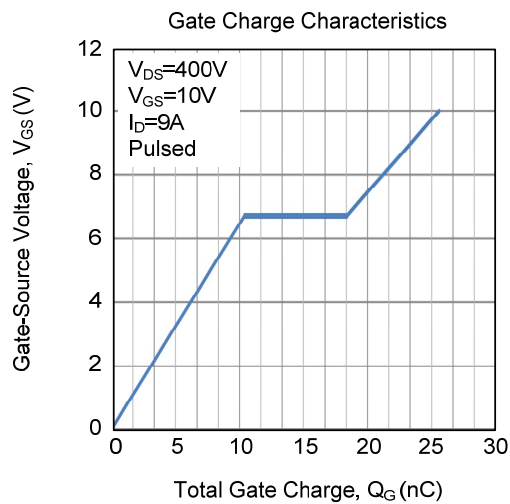
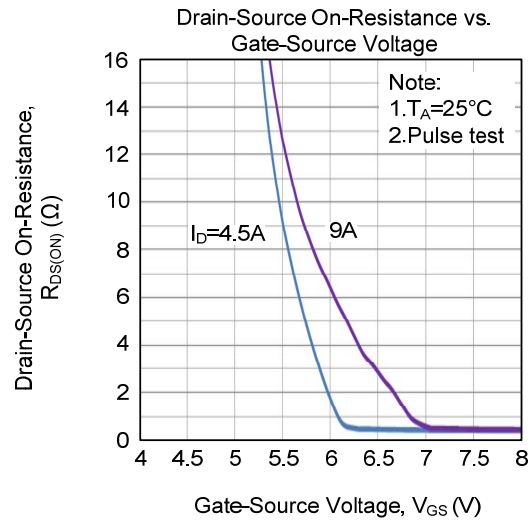
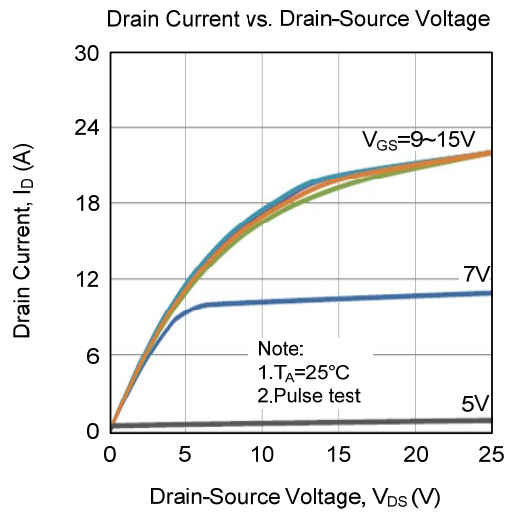


Unclamped Inductive Switching Test Circuit

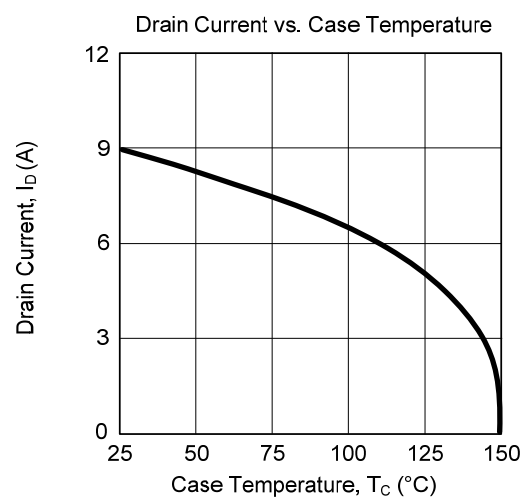
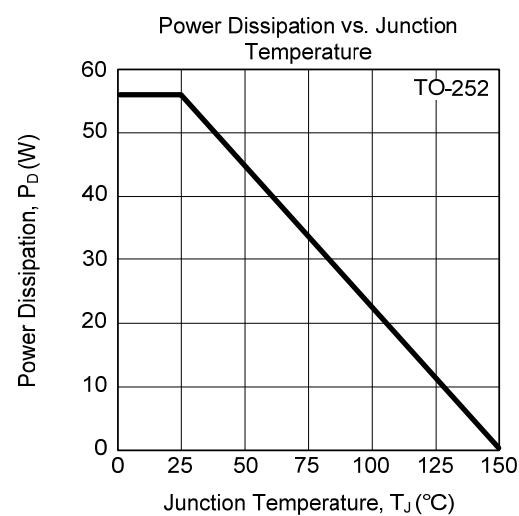
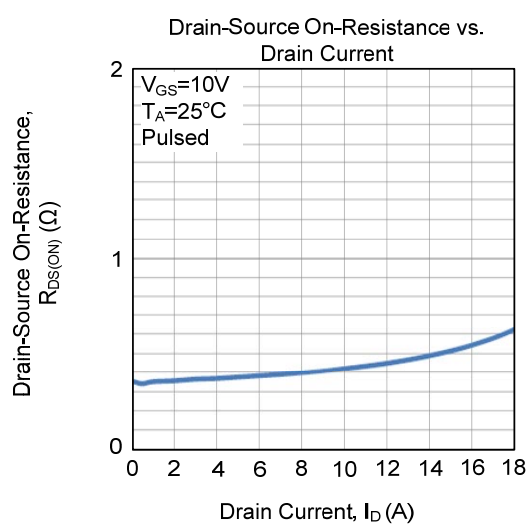
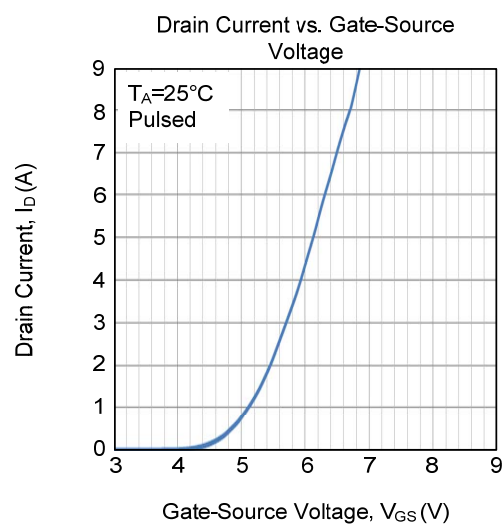
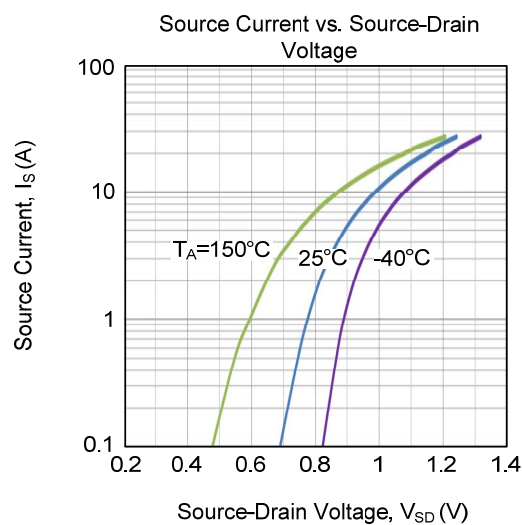
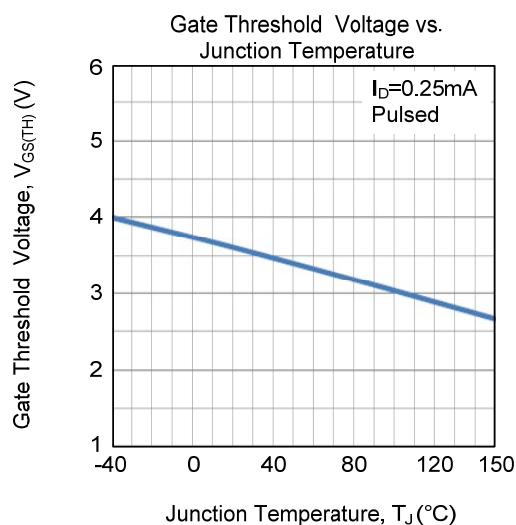


Unclamped Inductive Switching Waveforms

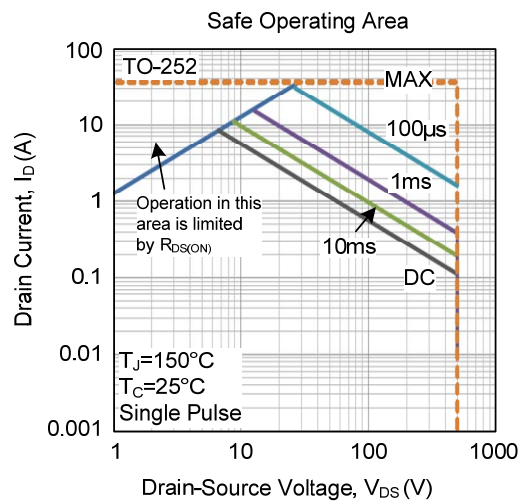
TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS (Cont.)



TYPICAL CHARACTERISTICS (Cont.)



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